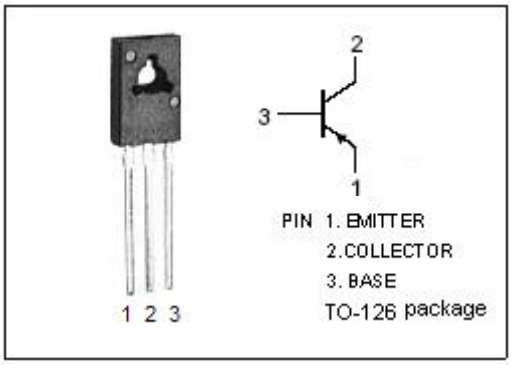
isc Silicon PNP Power Transistor — BD286

DESCRIPTION

- Collector-Emitter Sustaining Voltage -
  : $V_{CEO(SUS)}$= -45V(Min)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= -0.6V(Max)@ I_C = -2A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

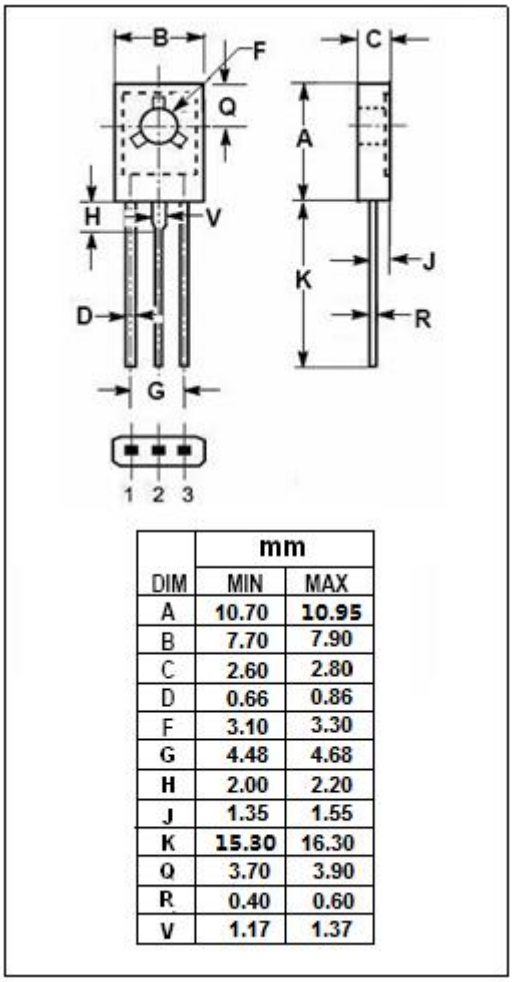


APPLICATIONS

- Designed for medium power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-45	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Pulse	-6	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ T_C=25℃	36	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-45			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-0.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -2A; V_{CE}= -1V			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -45V; I_E= 0			-100	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= -45V; V_{BE}= 0			-500	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-100	μA
h_{FE-1}	DC Current Gain	I_C= -10mA; V_{CE}= -5V	30			
h_{FE-2}	DC Current Gain	I_C= -0.5A; V_{CE}= -1V	85			
h_{FE-3}	DC Current Gain	I_C= -2A; V_{CE}= -1V	40			
f_T	Current-Gain—Bandwidth Product	I_C= -0.1A; V_{CE}= -5V	3			MHz